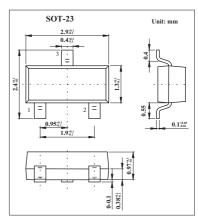
SMD Type Diodes

Silicon Schottky Barrier Diode HSM107S

■ Features

- Low VF and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	Vr	8	V
Peak forward current	Iғм	0.1	Α
Non-Repetitive Peak forward surge current	IFSM (Note 1)	0.5	Α
Average rectified current	lo	50	mA
Junction temperature	Tj	125	$^{\circ}$ C
Storage temperature	Tstg	-55 to +125	°C

Note

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse voltage	VR	VR =1.0 mA	8			pF
Reverse current	lr	VR = 5 V			30	μА
Forward voltage	VF	IF = 10 mA			0.3	V
ESD-Capability (Note 1)		C=200pF , Both forward and reverse direction 1 pulse.	100			V

Note

1. Failure criterion ; IR \geqslant 60 $\,\mu$ A at VR =5 V

■ Marking

Marking	C5
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^{1.} Square wave, 10ms